

Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12406-141US1	Application No. 10/561,318
	Applicant Rainer Butendeich et al.		
	Filing Date May 15, 2006	Group Art Unit 2814	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	5,825,052	10/20/1998	Shakuda	H01L	33/00	
	AB	2002/0053665	05/09/2002	Tsuda et al.	H01L	29/06	
	AC	2002/0149030	10/17/2002	Kean et al.	H01L	31/072	
	AD						
	AE						
	AF						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AG	GB 2 315 920	02/11/1996	Great Britain	H01L	21/208		
	AH							
	AI							
	AJ							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	AK	Copy of First Office Action of Chinese Patent Application No. 200480018204.2, dated June 8, 2007
	AL	K.L. Chang et al., "Effect of group II Impurity and group III native defect on disordering Cu-Pt type ordered structures In $\text{In}_{0.5}(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{P}$ layers", <u>Journal of Applied Physics</u> , Vol. 92, No. 11, pp. 6582-6589 (December 1, 2002)
	AM	<u>High Brightness Light Emitting Diodes</u> , Semiconductors and Semimetals, Vol. 48, eds. G.B. Stringfellow, M.G. Crawford, Academic Press (1997), pp. 1-45, 65-83, and 149-178
	AN	
	AO	

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	